EPSON

<u>S1F78520</u>

Charge-pump Step Down Regulator with Power Saving Mode

DESCRIPTION

The S1F78520 is a power IC which can generate two stabilized output voltages of 3.3 V (or 2.9 V or 2.5 V) and 2.5 V (or 2.0 V or 1.8 V) using the Li-ion battery. The 3.3 V range output is being generated through the LDO (series regulator). The 2.5 V range output is being generated through the charge pump type DC/DC converter consisting of built-in CMOS transistors. Since the voltages are being stabilized by adjustments of the charge pump DC/DC switching frequencies, higher conversion efficiencies as compared with the conventional series regulators can be acquired. Since the S1F78520 does not require external transistors, coils nor diodes, it is most suitable for the down sizing purpose and for reduction of the current consumption.

■ FEATURES

Supply voltage	· 3.6 V (2.7 V to 5.5 V) single power input
Voltage conversion method	• (1) LDO (series regulator)
	② Voltage dropping type charge pump
Output voltages	\cdot (1) 3.3 V or 2.9 V or 2.5 V \pm 3%
	$\textcircled{2}$ 2.5 V or 2.0 V or 1.8 V \pm 4%
	(output voltage is external pin setting)
Output current (Normal state/Standby state)	• ① Max. (100 mA/1 mA)
	② Max. (80 mA/100 μA)
Conversion efficiency	\cdot (1) 90% (the conversion from 3.6V to 3.3V)
	② 85% (peak efficiency)
Shut down current	· 1 μΑ
Self-consumption current	· 75 μA (under no load state)
Built-in self-consumption current suppressing funct	ion by use of standby (light load) signals
Self-consumption current	· 25 μA (under no load state)
Output voltage (2) switching frequency	• 450kHz
Built-in power good detector (equipped with the del	ay setting function)
Built-in low voltage detecting circuit (For setting of the sett	e detecting voltages, either of the internal setting fixed to
the IC or the external pin setting is selectable.)	

- Shipping state ------ SSOP3-24pin
- This IC is not of the radiation resistant design nor of the light resistance design.

Rev. 1.2

BLOCK DIAGRAM

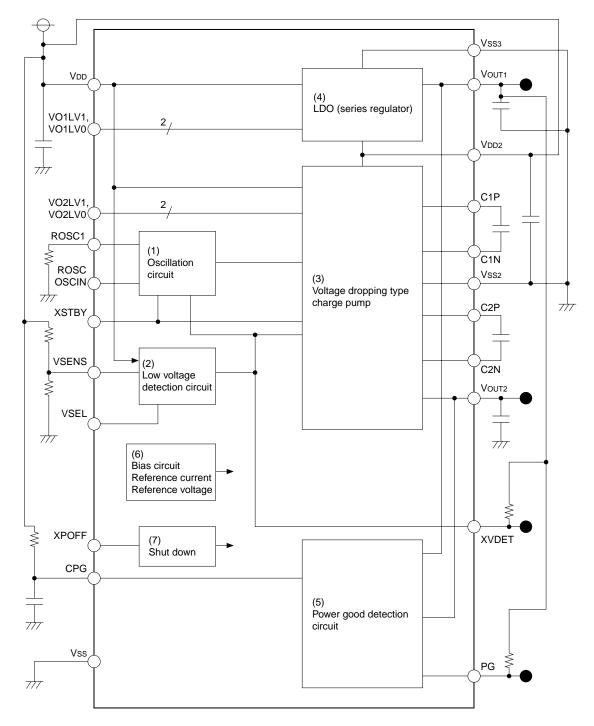


Fig. 1 Block diagram

DESCRIPTIONS FOR THE BLOCK DIAGRAM

(1) Oscillation circuit

This is the circuit to make oscillations by connecting a resistance to the ROSC1 pin and by supplying a constant current.

(2) Low voltage detection circuit

This circuit makes low voltage detections by monitoring the input voltage through the VDD pin. Provision of a hysteresis width is effective to prevent occurrences of unstable outputs (causing oscillations) while performing low voltage detecting operations. For setting of the detecting voltages, use of either of the internal voltage setting fixed to the IC or the external voltage setting pin VSENS is selectable through the VSEL pin.

(3) Voltage dropping type charge pump

The specified voltage is being output by voltage drops effected by the charge pump upon the inputted supply voltage VDD* - VSS* and using the VSS* potential as the reference voltage. The specified voltage is selectable (2.5 V or 2.0 V or 1.8 V) through the external pins VO2LV1, VO2LV0.

Also, the voltages are being stabilized by adjusting the switching frequencies of the charge pump. This circuit can drastically suppress the current consumption under the standby mode (light load).

(4) LDO (series regulator)

It stabilizes the voltage of the levels below the input supply voltage. The specified voltage is selectable (3.3 V or 2.9 V or 2.5 V) through the external pins VO1LV1, VO1LV0.

(5) Power good detection circuit

This circuit detects the power good signals when the output pins VOUT1 and VOUT2 are satisfying the specified voltage. Delay setting can be made for the power good signals by connecting a capacitor and a resistor to the external setting pin CPG.

(6) Bias circuit

This circuit generates the reference voltage and reference current which are necessary for this IC.

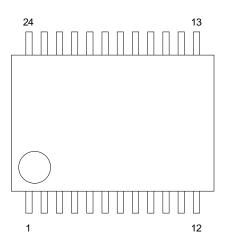
(7) Shut down

Operations of all the circuits can be interrupted by setting the shut down pin XPOFF to the Vss* level.

<Note> VDD* = VDD, VDD2, VSS* = VSS, VSS2, VSS3

■ PIN ASSIGNMENT

SSOP3-24pin S1F78520M0A01



Pin No.	Pin name	Pin No.	Pin name
1	XPOFF	13	XVDET
2	VO2LV1	14	VSENS
3	VO2LV0	15	Vdd
4	C1N	16	VSEL
5	C1P	17	Vss3
6	VOUT2	18	VOUT1
7	PG	19	VDD2
8	CPG	20	C2P
9	ROSC1	21	C2N
10	Vss	22	VO1LV0
11	OSCIN	23	VO1LV1
12	XSTBY	24	VSS2

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■ PIN DESCRIPTION

(1) Function pins

Pin name	I/O	Pin No.	Function				
VO1LV1	I	23	VOUT1 Output voltage level		designating	pin.	
			Pin se	etting	Output		
			VO1LV1	VO1LV0	voltage		
			Vss* level	Vss* level	3.3V		
VO1LV0		22	Vss* level	VDD* level	2.9V		
			VDD* level	Vss* level	2.5V		
			VDD* level	VDD* level	Not for use		
VO2LV1	1	2	VOUT2 Output	voltage level	designating	pin.	
			Pin se	etting	Output		
			VO2LV1	VO2LV0	voltage		
			Vss* level	Vss* level	2.5V		
VO2LV0		3	Vss* level	VDD* level	2.0V		
			VDD* level	Vss* level	1.8V		
			VDD* level	VDD* level	Not for use		
ROSC1	0	9	Pin to connect	the external	resistor for a	djustment of the oscillating current.	
XSTBY	I	12	This is the stan	dby pin. Un	der the stand	by mode (light load), the internal structure	
				e operated by	y low current	consumption when this signal is set to the	
_			Vss* level.				
VSENS		14	-		•	w voltage detection circuit. This is effec-	
		10	tive only when		-	-	
VSEL		16	-		•	w voltage detection circuit. NS becomes valid when this pin is set to	
			-		• •	enerated inside the IC becomes valid	
			when this pin is				
XPOFF	1	1				the VDD* level while the IC is in operation.	
			Operations of a	all the circuits	s will be inter	rupted when this signal is set to the $Vss*$	
					e shut down	state and making the output pins XVDET,	
0.50	<u> </u>		PG to open sta				
CPG C1P	 0	8	Delay time sett	• •			
CIP	0	5	output voltage.	•	nor the hying	g capacitor C1 for generation of the VOUT2	
C1N	0	4			n for the flyin	g capacitor C1 for generation of the VOUT2	
			output voltage.		······································	g p	
C2P	0	20	Positive side co	onnection pir	for the flying	g capacitor C2 for generation of the VOUT2	
			output voltage.				
C2N	0	21	-	•	n for the flying	g capacitor C2 for generation of the VOUT2	
WOFT		40	output voltage.			the law of the second state of the state of the The	
XVDET	0	13	output state is			the low voltage detection circuit. The	
				•		power pin VDD is at the low voltage level.	
PG	0	7				output power pins VOUT1 and VOUT2.	
-			The output stat	v v	•		
				•		tput power pins are satisfying the speci-	
			fied voltage.				

(2) Power pins

Pin name	I/O	Pin No.	Function
Vdd	I	15	Positive side input power pin.
Vdd2	I	19	Positive side input power pin.
Vss	I	10	Negative side input power pin.
VSS2	I	24	Negative side input power pin.
Vss3	I	17	Negative side input power pin.
VOUT1	0	18	LDO (series regulator) output power pin.
Vout2	0	6	Voltage dropping type charge pump output power pin.

<Note 1> Connect the VDD and VDD2 each other externally and keep them at the same potential level.

<Note 2> Connect the Vss < Vss2 and Vss3 each other externally and keep them at the same potential level.

(3) Testing pin

Pin name	I/O	Pin No.	Function	
OSCIN	I	11	VDD* level is normally fixed or open.	

■ FUNCTIONAL DESCRIPTION

Operational description

S1F78520 is a power supply IC which generates two output voltages, 3.3V (or 2.9V or 2.5V) and 2.5V (or 2.0V or 1.8V), stabilized from Li-ion batteries. High conversion efficiencies can be aquired under heavy loads by standby input signal. While low consuming current operations can be realized under light load state.

Generating voltage levels are:

- LDO (series regulator) output voltage [3.3 V or 2.9 V or 2.5 V]*1 (VOUT1)
- Voltage dropping type charge pump output voltage [2.5 V or 2.0 V or 1.8 V]*2 (VOUT2)
- *1: Selection of 3.3 V or 2.9 V or 2.5 V is to be designated by use of the external pins VO1LV1, VO1LV0.
- *2: Selection of 2.5 V or 2.0 V or 1.8 V is to be designated by use of the external pins VO2LV1, VO2LV0.

The VOUT1 output voltage is being generated by stabilizing the potential difference occurring between "VDD* – VSS*" using the VSS* potential as the reference voltage.

While the VOUT2 voltage is being generated after selection of the optimum voltage dropping ratio among difference ent voltage dropping ratios for the voltage dropping type charge pump to let it work on the potential difference occurring between "VDD* – VSS*" using the VSS* potential as the reference voltage and stabilizing the voltage by fine adjustments of the switching frequencies. Since an extra voltage stabilizing circuit is not being used for the output, high conversion efficiencies can be acquired.

Indicated below is the system configuration diagram for the power circuit.

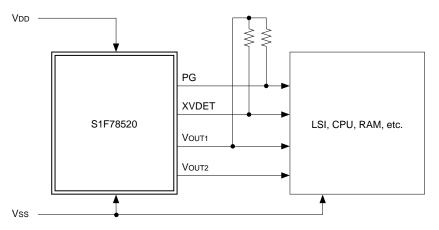


Fig. 2 System configuration diagram

Oscillation circuit

The S1F78520 incorporates an oscillation circuit for the voltage dropping clock. This circuit is to be used connecting the oscillation current adjusting external resistor ROSC between the ROSC1 pin and the Vss. The oscillation circuit will stop operation under shut down state (XPOFF = Vss* level). Also, the oscillation will be interrupted by setting the ROSC1 pin to the VDD* level or by making the pin into open state. As the oscillation current adjusting external resistance, we recommend use of ROSC = 1MEG Ω .

Standby mode

By setting the standby mode signal XSTBY externally, current consumption of this IC can be suppressed drastically.

The time required after the mode change is made with the standby pin until the internal mode of the IC is stabilized should be max. 10ms to min. 0s. Complete timing design should be effected when using the standby mode.

XSTBY pin	Mode name Max. output current		Self-consumption current
			(Under no load state)
VDD* level	Normal mode	Vout1 : 100 mA	75 μA
	(Under heavy load state)	Vout2 : 80 mA	75 μΛ
Vss* level	Standby mode	Vout1 : 1 mA	25 μA
	(Under light load state)	Vout2 : 100 μA	25 μΑ

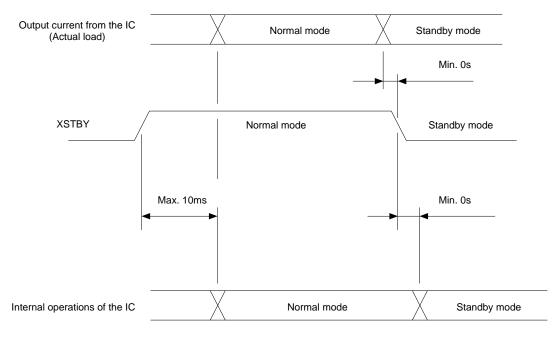


Fig. 3 below indicates a mode changing timing example.

Low voltage detection circuit

This circuit makes low voltage detections by monitoring the input voltage through the VDD pin. For setting of the detecting voltages, use of either of the internal voltage setting fixed to the IC or the external voltage setting pin VSENS is selectable through the external input pin VSEL.

VSEL pin	Detecting voltage selection	Detecting voltage value
Vss* level	External pin VSENS	-VDET: (According to the formula 2)
		+VDET: (According to the formula 4)
VDD* level	Internal voltage setting fixed	-VDET: 3.30 V
	to the IC	+VDET: 3.39 V

The detecting voltage (–VDET) in case of external voltage setting will be the VDD voltage value satisfying the following formulae.

 $VREF1 \ge VDD \bullet (Rb)/(Ra + Rb) = VSENS \dots$ (Formula 1)

Consequently,

 $VDD \leq VREF1 \bullet (Ra + Rb)/(Rb) [V] \dots$ (Formula 2)

can be established.

Also, the cancelling voltage (+VDET) in case of external voltage setting will be the VDD voltage value satisfying the following formulae.

 $VREF2 \leq VDD \bullet (Rb)/(Ra + Rb) = VSENS$ (Formula 3)

Consequently,

 $VDD \ge VREF2 \bullet (Ra + Rb)/(Rb) [V]$(Formula 4)

can be established.

Fig. 4 below shows the block diagram for the external setting.

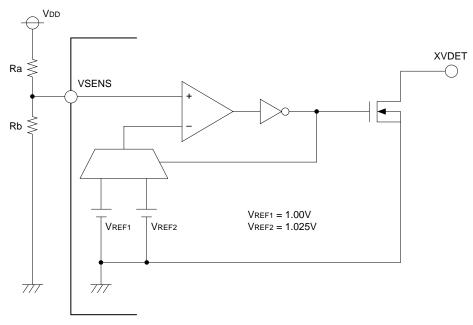


Fig. 4 Block diagram for the external setting

Power good detection circuit

Power good signals are detected when both of the output pins VOUT1 and VOUT2 are satisfying the specified voltage.

As for the power good detection range, provision of a hysteresis width for the lower limit value of detection according to Fig. 5 indicated below is effective to prevent occurrences of unstable power good signal outputs in the neighborhood of the detection limit value range.

Also, delay setting can be made for the power good signals by use of the capacitor CDPG and the resistor RDPG. When the output voltage rises beyond the cancelling voltage, charge to the external capacitor will begin. When the capacitor voltage rises beyond the delaying threshold valve voltage, the power good signal changes from the Vss* level to open state.

The delaying time can be calculated by formula 5.

Fig. 6 is an outline drawing for delay settings and Fig. 7 is the connection diagram in the neighborhood of the power good detection circuit.

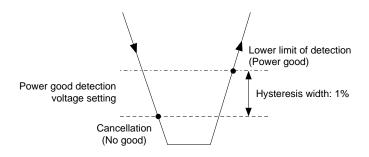


Fig. 5 Power good detecting range

Delay time (TDPG) can be calculated with the formula as below using external resistance (RDPG) and capacitor (CDPG).

TDPG (S) $\ =\$ CDPG (F) \times RDPG (Ω).....(Formula 5)

Example :

 $CDPG = 0.1\mu F, RDPG = 1MEG\Omega$ $TDPG = 0.1\mu F \times 1MEG\Omega = 0.1 (S)$

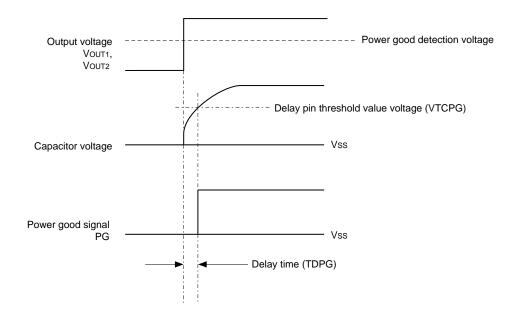


Fig. 6 Outline drawing for delay settings

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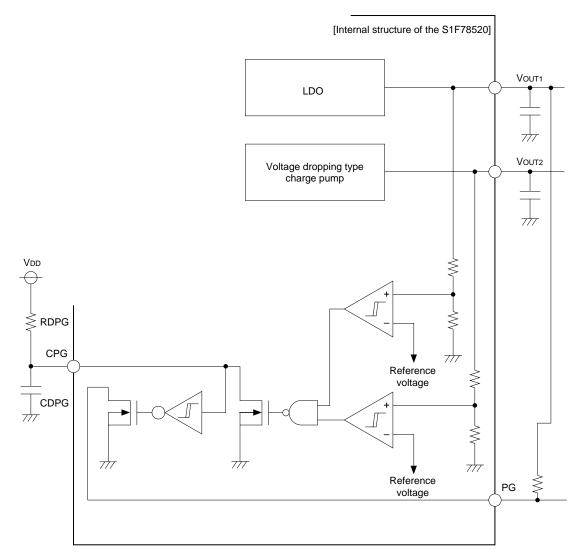


Fig. 7 Connection diagram in the neighborhood of the power good detection circuit

l to mo	Symbol	Rat	ing	11	Annlinghle nin	Demerike	
ltem	Symbol	Min.	Max.	Unit	Applicable pin	Remarks	
Input supply voltage	Vdd	-0.3	7.0	V VDD, VDD2			
Output voltage 1	VOUT1	-0.3	7.0	V	Vout1,	_	
Output voltage 2	Vout2	-0.3	7.0	V	VOUT2	_	
Input pin voltage	Vin	-0.3	VDD+0.3	V	<note 1=""></note>		
Input current	IVdd	_	— 240 mA Vi		Vdd, Vdd2	_	
Output current 1	IVOUT1		120	mA	VOUT1	_	
Output current 2	IVOUT2	— 100		mA	VOUT2	_	
Allowable dissipation	PD	_	520	mW	—	Ta = 25 °C	
Operating temperature	Topr	-30	85	°C	—	_	
Storage temperature	Tstg	-55	150	°C	—	_	
Soldering temperature and time	Tsol		260 · 10	°C · s	_	At leads	

■ ABSOLUTE MAXIMUM RATINGS

<Note 1> The applicable pins are VO1LV1, VO1LV0, VO2LV1, VO2LV0, XSTBY, VSENS, VSEL, XPOFF, CPG and OSCIN.

<Note 2> Do not apply external voltage to the output pins and the pin connecting to the capacitor.

<Note 3> Use of the IC under any conditions exceeding the above absolute maximum ratings may cause malfunctioning or permanent breakdown. Or, even if the IC may operate normally temporarily, the reliability may greatly drop.

■ ELECTRICAL CHARACTERISTICS

DC characteristics

OLDO (series regulator), voltage dropping type charge pump

In case particular designations are not made (Note 1): Ta = 25 °C

	Symbol			Rating			
Item		Conditions	Min.	Тур.	Max.	Unit	Remarks
Input supply voltage	Vdd	Applicable pin: VDD	2.7	3.6	5.5	V	_
High level input voltage	Viн	_	0.7*Vdd		Vdd	V	2
Low level input voltage	VIL		0	_	0.3*Vdd	V	2
Input leak current	ILIN	$Vss \le VI \le VDD$ $VDD = 3.6 V$	-0.5	_	0.5	μA	3
Output voltage 11	Vout11	Applicable pin: VOUT1 Output voltage setting: 3.3 V VDD = 3.6 V IVOUT1 = 10 mA	3.20	3.30	3.40	V	_
Output voltage 12	Vout12	Applicable pin: VOUT1 Output voltage setting: 2.9 V VDD = 3.6 V IVOUT1 = 10 mA	2.81	2.90	2.99	V	_
Output voltage 13	Vout13	Applicable pin: VOUT1 Output voltage setting: 2.5 V VDD = 3.6 V IVOUT1 = 10 mA	2.42	2.50	2.58	V	_
Output voltage 21	VOUT21	Applicable pin: VOUT2 Output voltage setting: 2.5 V VDD = 3.6 V IVOUT2 = 10 mA	2.40	2.50	2.60	V	_
Output voltage 22	Vout22	Applicable pin: VOUT2 Output voltage setting: 2.0 V VDD = 3.6 V IVOUT2 = 10 mA	1.92	2.00	2.08	V	_
Output voltage 23	Vout23	Applicable pin: VOUT2 Output voltage setting: 1.8 V VDD = 3.6 V IVOUT2 = 10 mA	1.72	1.80	1.88	V	_
Output voltage 11	IVOUT11	Applicable pin: VOUT1 Output voltage setting: 3.3 V VDD = 3.6 V	_	_	100	mA	_
Output voltage 12	IVOUT12	Applicable pin: VOUT1 Output voltage setting: 2.9 V VDD = 3.6 V	_		100	mA	_
Output voltage 13	IVout13	Applicable pin: VOUT1 Output voltage setting: 2.5 V VDD = 3.6 V	_		100	mA	_

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				Rating			. .
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Remarks
		Applicable pin: VOUT2					
Output voltage 21	IVOUT21	Output voltage setting: 2.5 V		_	80	mA	_
		VDD = 3.6 V					
		Applicable pin: VOUT2					
Output voltage 22	IVOUT22	Output voltage setting: 2.0 V	_	_	80	mA	_
		VDD = 3.6 V					
		Applicable pin: VOUT2					
Output voltage 23	IVOUT23	Output voltage setting: 1.8 V	_	_	80	mA	_
		VDD = 3.6 V					
		VDD = 3.6 V					
Load stability 1	$\frac{\Delta VOUT1}{\Delta IOUT1}$	Output voltage setting: 3.3 V	_	30	45	mV	_
		$0 \text{ mA} \le \text{IOUT1} \le 50 \text{ mA}$					
		VDD = 3.6 V		20	30	mV	
Load stability 2	$\frac{\Delta VOUT2}{\Delta IOUT2}$	Output voltage setting: 1.8 V	_				_
		$0 \text{ mA} \le IOUT2 \le 25 \text{ mA}$					
		VDD = 3.0 V			150		
I/O voltage difference	VDIF	IOUT1 = 30 mA	-	80		mV	—
	RV0UT2	VDD = 2.5 V		6.5		Ω	
Output impedance		IOUT2 = 10 mA					—
	IOP1	VDD = 3.6 V, no load				μA	
Current consumption 1		Normal mode	-	75	90		
	IOP2	VDD = 3.6 V, no load	-	25	40	μA	
Current consumption 2		Standby mode					
Resting current	10	VDD = 3.6 V			4.0		
	IQ	Shut down mode	-	_	1.0	μA	_
	$\Delta VOUT1$	$3.6 \text{ V} \leq \text{VDD} \leq 4.6 \text{ V}$				0/12/	
Input stability 1	ΔV dd	IOUT1 = 50 mA	-	0.4	0.8	%/ V	_
	Δ VOUT2	$3.6 \text{ V} \leq \text{VDD} \leq 4.6 \text{ V}$				0/12/	
Input stability 2	ΔV DD	IOUT2 = 25 mA	-	0.3	0.6	%/ V	_
Power conversion	D ((Normal mode		0.5			
efficiency (Charge pump)	Peff	IVOUT2 = 40 mA	-	85		%	4
Output voltage /	Δ VOUT1	IVOUT2 = 50 mA		1000			
temperature coefficient 1	ΔTopr	–30 °C ≤ Topr ≤ 85°C	-	±300		ppm/°C	_
Output voltage /	ΔVOUT2	IVOUT2 = 0.05 mA		1000		100	
temperature coefficient 2	ΔTopr	–30 °C ≤ Topr ≤ 85°C	-	±300	-	ppm/°C	

<Note 1> Conditions on the operation mode, external parts constant, pins, etc. in case particular designations are not made are as follows:

Connection and parts constant : Standard connection 1

XPOFF pin : XPOFF = HIGH (Normal mode)

: XSTBY = HIGH (Normal mode)

<Note 2> The applicable pins are V01LV1, V01LV0, V02LV1, V02LV0, XSTBY, VSEL, XPOFF.

<Note 3> The applicable pins are V01LV1, V01LV0, V02LV1, V02LV0, CPG, XSTBY, VSENS, VSEL, XPOFF.

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<Note 4> The power conversion efficiency of the voltage dropping type charge pump only.

Rev. 1.2

XSTBY pin

OLow voltage detection

Item	Cumhal	Canditiana	Rating			Unit	
Item	Symbol	Conditions	Min.	Тур.	Typ. Max.		Remarks
Detection voltage		VSEL pin = VDD* level	3.20	3.30	3.40	V	
Detection voltage	-VDET	(Internal voltage setting fixed to the IC)	0.20	0.00	0.40	ľ	
		VSEL pin = VDD* level	0.01	0.09	0.18	V	
Hysteresis width	VHYS	(Internal voltage setting fixed to the IC)	0.01	0.03	0.10	Ň	
Reference detection		VSEL pin = Vss* level	0.97	1.00	1.03	V	
voltage 1	VREF1	(External voltage setting to the VSENS pin)	0.97	1.00	1.03	v	
Reference detection		VSEL pin = Vss* level	0.99	1.025	1.055	v	
voltage 2		(External voltage setting to the VSENS pin)	0.99	1.025	1.000	, v	
	VVDDL	Topr = 25 °C	_	—	1.5	V	2
Min. operating voltage		–30 °C ≤ Topr ≤ 85 °C	—	—	1.53		2
Output current		VDD = 3.6 V	0.00		_	mA	
(Driver output pin)	IVDET	XVDET = 0.1V	0.36	-			-
Off leak current	IVDOFF	VDD = XVDET = 5.5V	-150	0	450	nA	_
(Driver output pin)	IVDOFF	VDD = XVDET = 3.5V	-150		150		
Transfer delay time	TPLH				100		3
		_			100	μs	5
Detection voltage /	∆-VDET	VSEL pin = VDD* level					
temperature coefficient	$\Delta - VDET$ $\Delta Topr$	(Internal voltage setting fixed to the IC)		±300	_	ppm/°C	_
temperature ovenitient		–30 °C ≤ Topr ≤ 85 °C					

In case particular designations are not made (Note 1): Ta = 25 °C

<Note 1> Conditions on the operation mode, external parts constant, pins, etc. in case particular designations are not made are as follows:

Connection and parts constant	: Standard connection 1
XPOFF pin	: XPOFF = HIGH (Normal mode)
XSTBY pin	: XSTBY = HIGH (Normal mode)

<Note 2> The supply voltage value where the output voltage becomes 0.1V or less. (Pullup resistance : 470kΩ, Pullup voltage : 3.6V)

<Note 3> Time when the output voltage reaches 1.8V after applying the minimum operating voltage of \rightarrow 3.6V pulse voltage to VDD on the condition that pullup resistance is 470k Ω and pullup voltage is 3.6V.

OPower good detection

Item	Symbol	Conditions	Rating				
			Min.	Тур.	Max.	Unit	Remarks
Lower limit detection voltage 11	VDLPG11	Applicable pin = VOUT1					
		Output voltage setting: 3.3 V	2.82	2.91	3.00	V	_
		Hysteresis width: 1%					
Lower limit detection voltage 12	VDLPG12	Applicable pin = VOUT1					
		Output voltage setting: 2.9 V	2.54	2.62	2.70	V	
		Hysteresis width: 1%					
Lower limit detection voltage 13	VDLPG13	Applicable pin = VOUT1					
		Output voltage setting: 2.5 V	2.16	2.23	2.30	V	_
		Hysteresis width: 1%					
Lower limit detection voltage 21	VDLPG21	Applicable pin = VOUT2					
		Output voltage setting: 2.5 V	2.16	2.23	2.30	V	
		Hysteresis width: 1%					
Lower limit detection voltage 22	VDLPG22	Applicable pin = VOUT2	1.68	1.74	1.80	V	_
		Output voltage setting: 2.0 V					
		Hysteresis width: 1%					
Lower limit detection voltage 23	VDLPG23	Applicable pin = VOUT2	1.55	1.60	1.65	V	
		Output voltage setting: 1.8 V					
		Hysteresis width: 1%					
PG output current	IPG	VDD = 3.6V	0.36	_	_	mA	
(Driver output pin)		PG = 0.1V					
PG off leak current	IPGOFF	VDD = PG = 5.5V	-150	_	150	nA	_
(Driver output pin)		VDD = PG = 5:5V					
Delay pin	VTCPG	VDD = 3.6V 2	2.05	2.4	2.77	V	_
Threshold value voltage			2.05				
CPG output current	ICPG	VDD = 3.6V	0.06		_	mA	_
(Delay pin)		CPG = 0.1V					
Lower limit detection voltage/	∆VDLPG1	Applicable pin: VOUT1		±300	_	ppm/°C	_
temperature coefficient 1	∆Topr	–30 °C ≤ Topr ≤ 85 °C					
Lower limit detection voltage/ temperature coefficient 2	$\frac{\Delta \text{VDLPG21}}{\Delta \text{Topr}}$	Applicable pin: VOUT2	_	±300	_	ppm/°C	_
		Output voltage setting: 2.0 V					
		–30 °C ≤ Topr ≤ 85 °C					

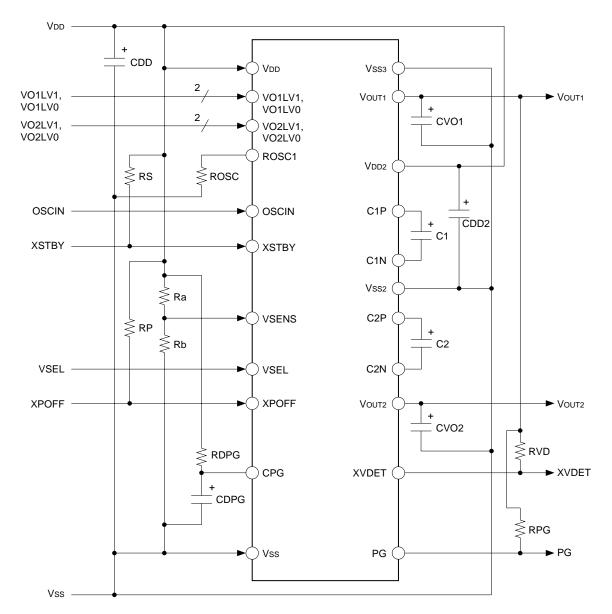
In case particular designations are not made (Note 1): Ta = 25 °C

<Note 1> Conditions on the operation mode, external parts constant, pins, etc. in case particular designations are not made are as follows:

Connection and parts constant : Standard connection 1 XPOFF pin XSTBY pin

- : XPOFF = HIGH (Normal mode)

: XSTBY = HIGH (Normal mode)



■ REFERENCE EXTERNAL CONNECTION (AN EXAMPLE)

Standard connection 1

Recommended values for the external parts ROSC = 1MEG Ω Ra = (Make the detection voltage setting according to the formulae 2 and 4.) Rb = (Make the detection voltage setting according to the formulae 2 and 4.) RS = RP = RVD = RPG = 470k Ω CDD = CDD2 = 4.7 μ F CDPG = 0.1 μ F [In case a delay time setting of 100ms is made.]

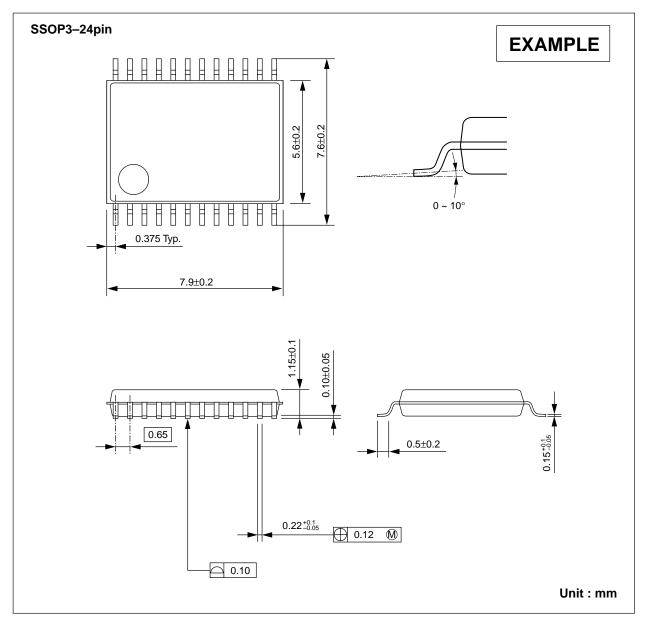
RDPG = $1MEG\Omega$ [In case a delay time setting of 100ms is made.]

 $CV01 = CV02 = 22\mu F$

 $C1 = C2 = 0.47 \mu F$

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■ DIMENSIONAL OUTLINE DRAWING



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